HFZT

SCS210AM

SiC Schottky Barrier Diode

VOLTAGE RANGE: 650V

Features

- Shorter recovery time
- Reduced temperature dependence
- High-speed switching possible

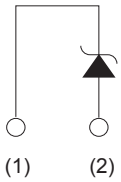
MECHANICAL DATA

- Case style:TO-220FM molded plastic
- Mounting position:any

●Outline

TO-220FM

●Inner circuit



(1) Cathode
(2) Anode

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V_{RM}	650	V
Reverse voltage (DC)	V_R	650	V
Continuous forward current	I_F	10*1	A
Surge no repetitive forward current	I_{FSM}	40*2	A
		150*3	A
		31*4	A
Repetitive peak forward current	I_{FRM}	26*5	A
Total power disspation	P_D	34*6	W
Junction temperature	Tj	175	°C
Range of storage temperature	Tstg	−55 to +175	°C

*1 Tc=84°C *2 PW=8.3ms sinusoidal, Tj=25°C *3 PW=10μs square, Tj=25°C
*4 PW=8.3ms sinusoidal, Tj=150°C *5 Tc=100°C, Tj=150°C, Duty cycle=10% *6 Tc=25°C

Electrical characteristics (Tj = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
DC blocking voltage	V_{DC}	I_R=0.2mA	600	-	-	V
Forward voltage	V_F	I_F=10A,Tj=25°C	-	1.35	1.55	V
		I_F=10A,Tj=150°C	-	1.55	-	V
		I_F=10A,Tj=175°C	-	1.63	-	V
Reverse current	I_R	V_R=600V,Tj=25°C	-	2	200	μA
		V_R=600V,Tj=150°C	-	30	-	μA
		V_R=600V,Tj=175°C	-	70	-	μA
Total capacitance	C	V_R=1V,f=1MHz	-	365	-	pF
		V_R=600V,f=1MHz	-	37	-	pF
Total capacitive charge	Qc	V_R=400V,di/dt=350A/μs	-	15	-	nC
Switching time	tc	V_R=400V,di/dt=350A/μs	-	15	-	ns

Thermal characteristics

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Thermal resistance	$R_{th(j-c)}$	-	-	3.6	4.3	°C/W

RATINGS AND CHARACTERISTIC CURVES

Fig.1 V_F - I_F Characteristics

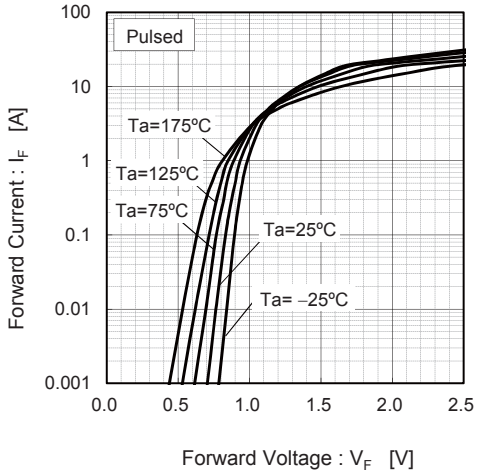


Fig.2 V_F - I_F Characteristics

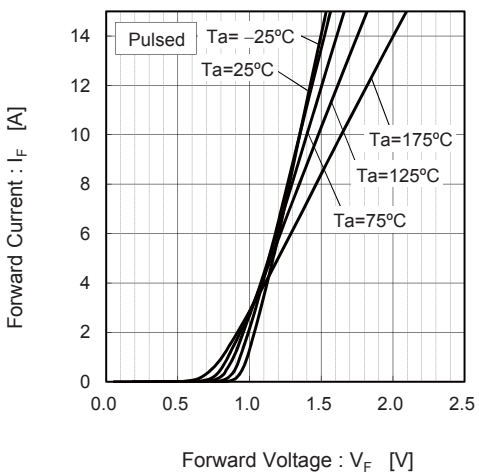


Fig.3 V_R - I_R Characteristics

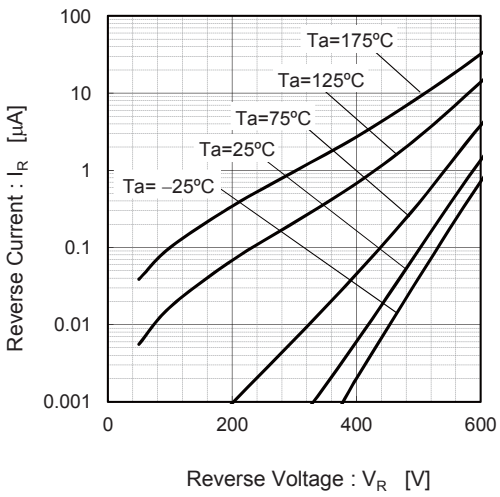


Fig.4 V_R-Ct Characteristics

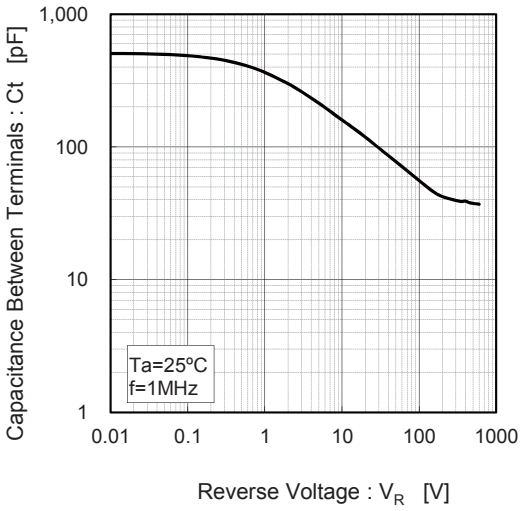


Fig.5 Thermal Resistance vs. Pulse Width

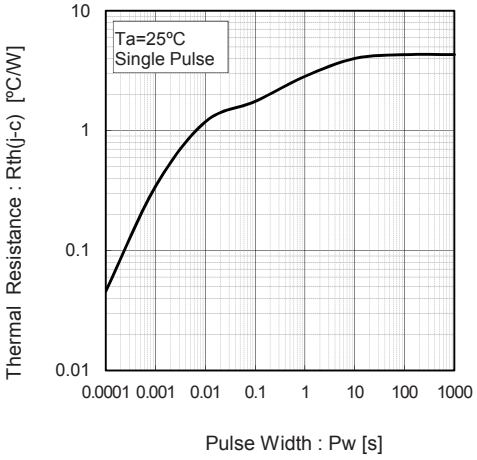


Fig.6 Power Dissipation

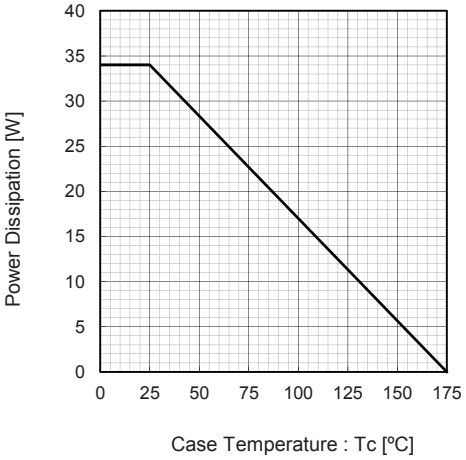


Fig.7 Derating Curve Ip-Tc

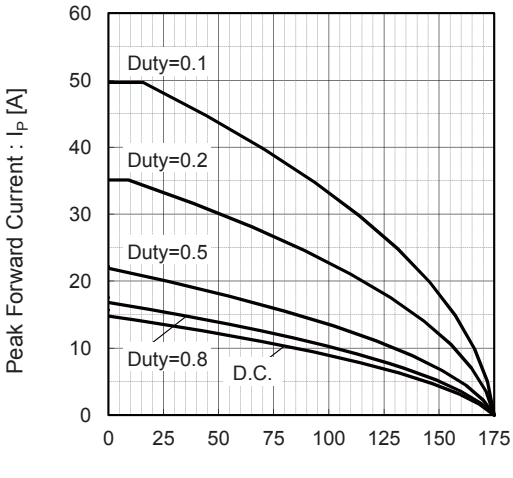


Fig.8 Io-Pf Characteristics